BLM9D2327-25B

LDMOS 2-stage integrated Doherty MMIC

AMPLEON

Rev. 1 — 1 September 2017

Product data sheet

1. Product profile

1.1 General description

The BLM9D2327-25B is a 2-stage fully integrated Doherty MMIC solution using Ampleon's state of the art GEN9 LDMOS technology. The carrier and peaking device, input splitter and output combiner are integrated in a single package. This multiband device is perfectly suited as general purpose driver or small cell final in the frequency range from 2300 MHz to 2700 MHz. Available in PQFN outline.

Table 1. Application performance

Typical RF performance tuned in a wideband 2300 MHz to 2700 MHz application board at $T_{case} = 25$ °C; $I_{Dq} = 76$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.81$ V. Test signal: 1-carrier LTE 20 MHz; PAR = 7.2 dB at 0.01% probability on CCDF.

Test signal	f	V _{DS}	P _{L(AV)}	Gp	η _D
	(MHz)	(V)	(W)	(dB)	(%)
single carrier LTE 20 MHz	2500	28	4.9	28.5	40.3

1.2 Features and benefits

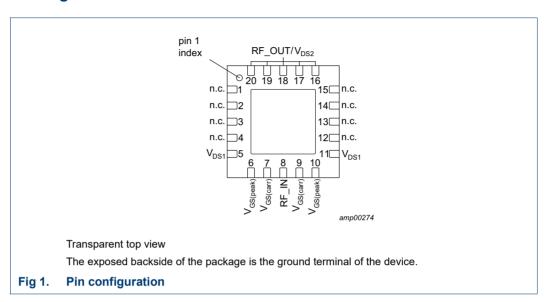
- Integrated input splitter
- Integrated output combiner
- High efficiency
- Designed for broadband operation (frequency 2300 MHz to 2700 MHz)
- Independent control of carrier and peaking bias
- Integrated ESD protection
- Source impedance 50 Ω ; high power gain
- Compliant to Directive 2002/95/EC, regarding restriction of hazardous substances (RoHS)

1.3 Applications

■ RF power MMIC for multi-carrier and multi-standard GSM, W-CDMA and LTE base stations in the 2300 MHz to 2700 MHz frequency range.

2. Pinning information

2.1 Pinning



2.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
n.c.	1	not connected
n.c.	2	not connected
n.c.	3	not connected
n.c.	4	not connected
V _{DS1}	5	drain-source voltage of driver stages
V _{GS(peak)}	6	gate-source voltage of peaking
V _{GS(carr)}	7	gate-source voltage of carrier
RF_IN	8	RF input
V _{GS(carr)}	9	gate-source voltage of carrier
V _{GS(peak)}	10	gate-source voltage of peaking
V _{DS1}	11	drain-source voltage of driver stages
n.c.	12	not connected
n.c.	13	not connected
n.c.	14	not connected
n.c.	15	not connected
RF_OUT/V _{DS2}	16	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	17	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	18	RF output / drain-source voltage of final stages

Table 2. Pin description ... continued

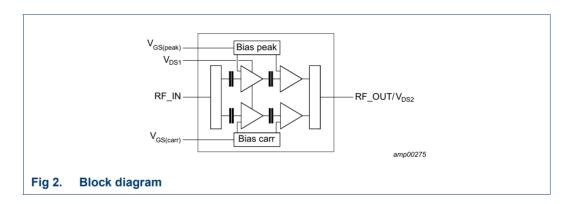
Symbol	Pin	Description
RF_OUT/V _{DS2}	19	RF output / drain-source voltage of final stages
RF_OUT/V _{DS2}	20	RF output / drain-source voltage of final stages
GND	flange	RF ground

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BLM9D2327-25B		plastic thermal enhanced quad flat package; no leads; 20 terminals; body 8.0 x 8.0 x 2.1 mm	SOT1462-1

4. Block diagram



5. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage		-	65	V
V_{GS}	gate-source voltage		-0.5	+13	V
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature	[1]	-	175	°C

^[1] Continuous use at maximum temperature will affect the reliability. For details refer to the online MTF calculator.

6. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter Conditions		Value	Unit	
R _{th(j-c)}	thermal resistance from junction to case	T_{case} = 90 °C; P_L = 4 W	[1]	11	K/W
		T _{case} = 90 °C; P _L = 2.5 W	[1]	12	K/W

^[1] When operated with a 1-carrier W-CDMA with PAR = 9.9 dB.

7. Characteristics

Table 6. DC characteristics

 $T_{case} = 25$ °C.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit		
Carrier								
V_{GSq}	gate-source quiescent voltage	$V_{DS} = 28 \text{ V}; I_D = 75 \text{ mA}$	1.7	2.1	2.7	V		
I _{GSS}	gate leakage current	V _{GS} = 1 V; V _{DS} = 0 V	-	-	140	nA		
Peaking	Peaking							
I _{GSS}	gate leakage current	V _{GS} = 1 V; V _{DS} = 0 V	-	-	140	nA		
Final stag	ges							
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μΑ		
Driver sta	Driver stages							
I _{DSS}	drain leakage current	V _{GS} = 0 V; V _{DS} = 28 V	-	-	1.4	μΑ		

Table 7. RF Characteristics

Typical RF performance at T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq} = 75 mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.7$ V; $P_{L(AV)}$ = 5 W.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Test sign	nal: pulsed CW					
G _p	power gain	f = 2700 MHz	25.5	27	28.5	dB
η_{D}	drain efficiency	P _L = 5 W (37 dBm)	34	38	-	%
		$P_L = P_{L(3dB)}$	50	54.5	-	%
RLin	input return loss		-	-20	-10	dB
P _{L(3dB)}	output power at 3 dB gain compression		44	44.6	-	dBm

8. Application information

Table 8. Typical performance

 $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 76$ mA (carrier and peaking). Test signal: 1-carrier LTE; PAR = 7.2 dB at 0.01 % probability CCDF; unless otherwise specified, typical performance in an Ampleon f = 2300 MHz to 2700 MHz frequency band symmetrical Doherty application circuit.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
P _{L(3dB)}	output power at 3 dB gain compression	f = 2500 MHz	[1]	-	44.9	-	dBm
φ _{s21} /φ _{s21(norm)}	normalized phase response	at 3 dB compression point; [2] - f = 2500 MHz		-	-5.9	-	0
η _D	drain efficiency	8 dB OBO (P _{L(AV)} = 36.9 dBm); f = 2500 MHz		-	40.3	-	%
Gp	power gain	P _{L(AV)} = 36.9 dBm; f = 2500 MHz		-	28.5	-	dB
B _{video}	video bandwidth	P _{L(AV)} = 36 dBm set to obtain IMD3 = -30 dBc; 2-tone CW; f = 2500 MHz		-	420	-	MHz
G _{flat}	gain flatness	P _{L(AV)} = 36.9 dBm; f = 2300 MHz to 2700 MHz		-	0.6	-	dB
ACPR _{20M}	adjacent channel power ratio (20M)	P _{L(AV)} = 36.9 dBm; f = 2500 MHz		-	-34.9	-	dBc
ΔG/ΔT	gain variation with temperature	f = 2500 MHz	[3]	-	0.04	-	dB/°C
К	Rollett stability factor	T _{case} = -40 °C; f = 0.2 GHz to 4.5 GHz	[3]	-	>2.2	-	

^[1] Pulsed CW power sweep measurement (δ = 10 %, t_p = 100 μ s).

^{[2] 25} ms CW power sweep measurement.

^[3] Small signal CW measurements.

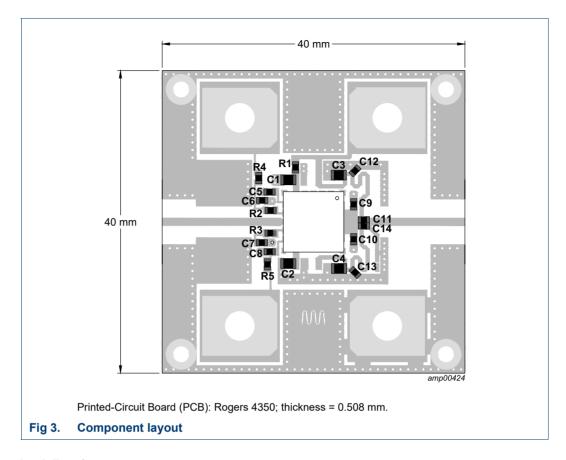
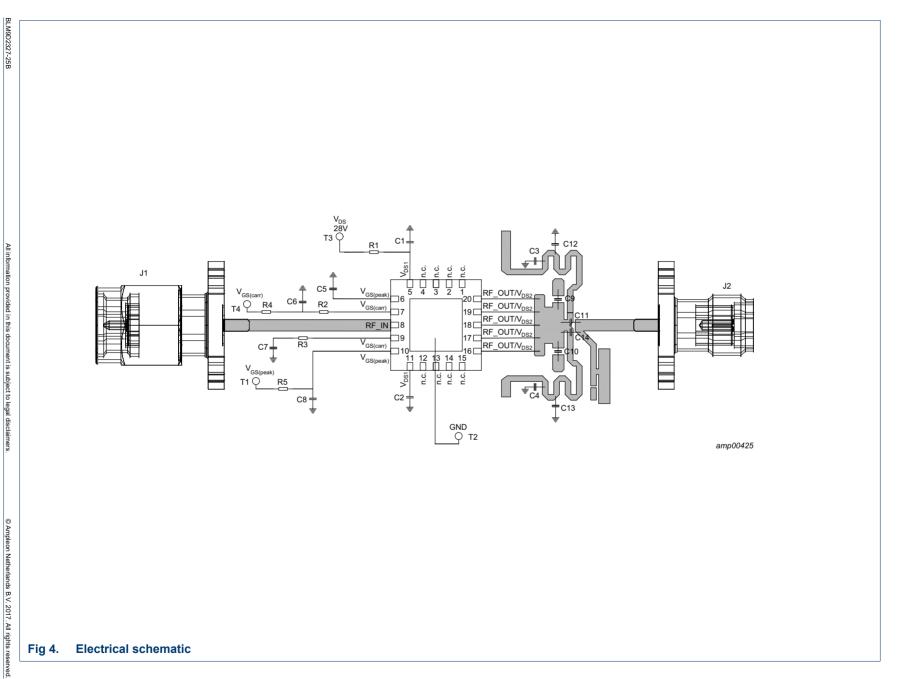


Table 9. Demo test circuit list of components

See Figure 3 for component layout.

Component	Description	Value	Remarks
C1, C2, C3, C4	multilayer ceramic chip capacitor	10 μF, 35 V	TDK: C2012X5R1V106M085ACL
C5, C6, C7, C8	multilayer ceramic chip capacitor	1 μF, 25 V	AVX: 06033D105KAT2A
C9, C10	multilayer ceramic chip capacitor	1.8 pF	Murata: GQM1875C2E1R6BB12
C11	multilayer ceramic chip capacitor	1.6 pF	Murata: GQM1875C2E5R6BB12
C12, C13	multilayer ceramic chip capacitor	9.1 pF	Murata: GQM1875C2E5R6BB12
C14	multilayer ceramic chip capacitor	0.5 pF	Murata: GQM1875C2E5R6BB12
J1	SMA Coaxial panel connector male		Hubner & Suhner: 13_SMA-50-0-2/111_N
J2	SMA Coaxial panel connector female		Hubner & Suhner: 23_SMA-50-0-2/111_N
R1	SMD resistor	0 Ω, ±1 %	Multicomp: MC805
R2, R3	SMD resistor	5.1 Ω, ±1 %	Multicomp: MC805
R4	SMD resistor	820 Ω, ±1 %	Multicomp: MC805
R5	SMD resistor	10 Ω, ±1 %	Multicomp: MC805
T1, T2, T3, T4	PCB Terminal	6.35 mm × 0.81 mm, 4.1 mm	TE connectivity



8.1 Ruggedness in a Doherty operation

The BLM9D2327-25B is capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions: V_{DS} = 32 V; I_{Dq} = 75 mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.7$ V; P_i corresponding to $P_{L(3dB)}$ under Z_S = 50 Ω load; f = 2700 MHz (1-carrier W-CDMA; PAR = 9.9 dB); T_{case} = 25 °C.

8.2 Impedance information

Table 10. Typical impedance for optimum Doherty operation

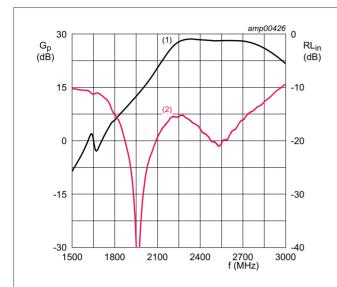
Measured load-pull data per section; test signal: pulsed CW; $T_{case} = 25$ °C; $V_{DS} = 28$ V; $I_{Dq} = 70$ mA (carrier); $V_{GSq(peaking)} = V_{GSq(carrier)} - 0.7$ V; $t_p = 100$ μ S; $\delta = 10$ %.

БЧ	t // dog(peaking	g) abq(camer)	, p	,					
	tuned for optimu	tuned for optimum Doherty operation							
f	Z _L	P _{L(3dB)}	G _{p(max)}	η _{add} [1]	η _{add} [2]				
(MHz)	(Ω)	(dBm)	(dB)	(%)	(%)				
2300	5.30 – j2.38	45.30	28.60	53.10	42.80				
2400	5.62 – j3.81	45.30	29.00	55.00	44.10				
2500	6.34 – j4.52	45.20	29.40	57.00	45.00				
2600	7.67 – j4.10	45.00	29.40	59.10	43.50				
2700	7.25 – j2.89	44.90	28.70	58.90	40.70				

^[1] at 44.5 dBm.

^[2] at 36.5 dBm.

8.3 Graphs



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 76 \text{ mA (carrier stages)};$

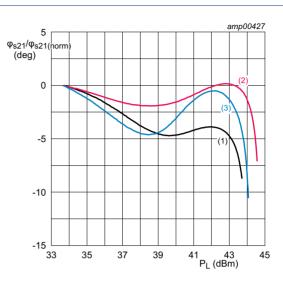
V_{GS} = 2.46 V (carrier stage);

V_{GS} = 1.65 V (peaking stage).

Test signal: CW.

- (1) magnitude of G_p
- (2) magnitude of RLin

Fig 5. Wideband power gain and input return loss as function of frequency; typical values



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 76 \text{ mA (carrier stages)};$

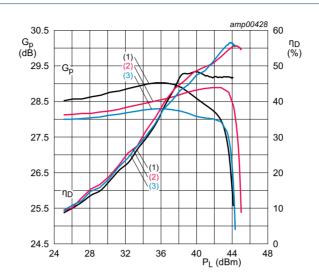
V_{GS} = 2.46 V (carrier stage);

V_{GS} = 1.65 V (peaking stage).

Test signal: 25 ms CW power sweep.

- (1) f = 2300 MHz
- (2) f = 2500 MHz
- (3) f = 2700 MHz

Fig 6. Normalized phase response as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 76 mA (carrier stages);

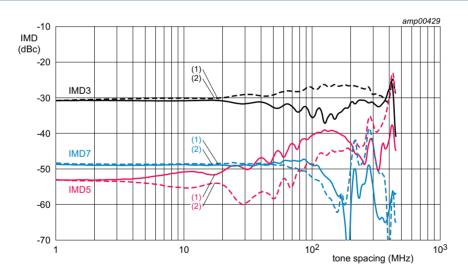
V_{GS} = 2.46 V (carrier stage);

 $V_{GS} = 1.65 \text{ V}$ (peaking stage).

Test signal: pulsed CW power sweep (δ = 10 %; t_p = μ s).

- (1) f = 2300 MHz
- (2) f = 2500 MHz
- (3) f = 2700 MHz

Fig 7. Power gain and drain efficiency as function of output power; typical values

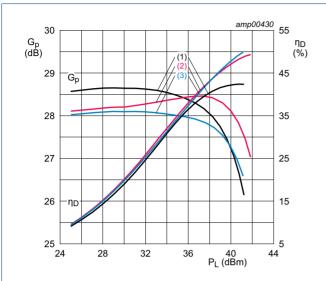


 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 76 mA (carrier stages); V_{GS} = 2.46 V (carrier stage); V_{GS} = 1.65 V (peaking stage); $P_{L(AV)}$ = 4 W.

Test signal: 2-tone CW; f_c = 2500 MHz.

- (1) IMD low
- (2) IMD high

Fig 8. Intermodulation distortion as a function of tone spacing; typical values



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 76 \text{ mA (carrier stages)};$

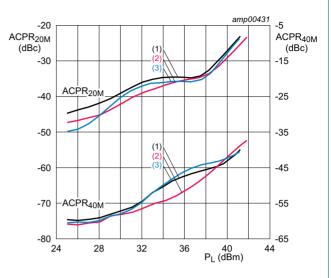
 $V_{GS} = 2.46 \text{ V (carrier stage)};$

V_{GS} = 1.65 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.2 dB at 0.01 % probability CCDF.

- (1) f = 2300 MHz
- (2) f = 2500 MHz
- (3) f = 2700 MHz

Fig 9. Power gain and drain efficiency as function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V;

 $I_{Dq1} + I_{Dq2} = 76 \text{ mA (carrier stages)};$

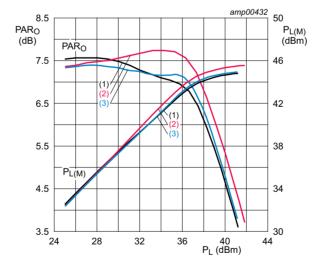
 $V_{GS} = 2.46 \text{ V (carrier stage)};$

V_{GS} = 1.65 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.2 dB at 0.01 % probability CCDF.

- (1) f = 2300 MHz
- (2) f = 2500 MHz
- (3) f = 2700 MHz

Fig 10. Adjacent channel power ratio as a function of output power; typical values



 T_{case} = 25 °C; V_{DS} = 28 V; I_{Dq1} + I_{Dq2} = 76 mA (carrier stages); V_{GS} = 2.46 V (carrier stage); V_{GS} = 1.65 V (peaking stage).

Test signal: 1-carrier LTE; PAR = 7.2 dB at 0.01 % probability CCDF.

- (1) f = 2300 MHz
- (2) f = 2500 MHz
- (3) f = 2700 MHz

Fig 11. Output peak-to-average ratio and peak output power as function of output power; typical values

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9. Package outline

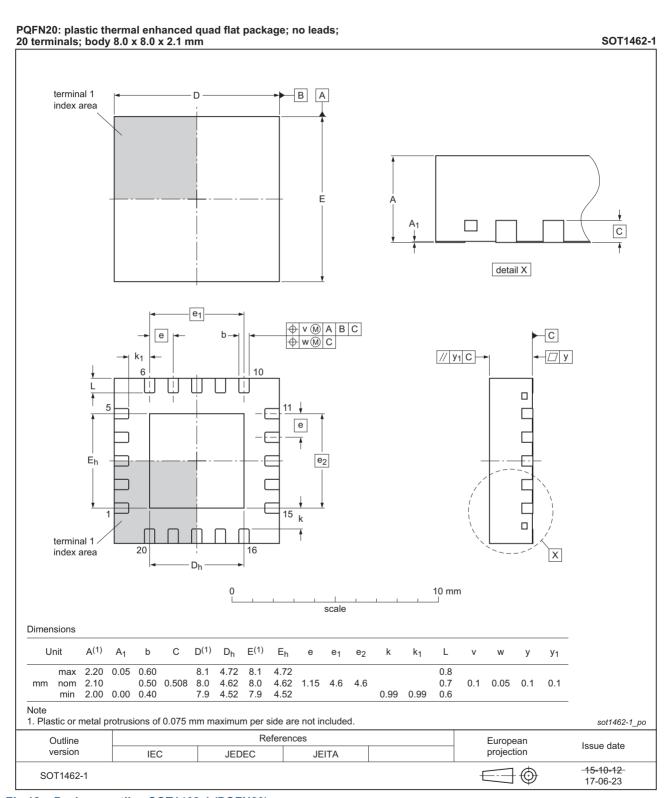


Fig 12. Package outline SOT1462-1 (PQFN20)

10. Handling information

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 11. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	1B 🔼

- [1] CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.
- [2] HBM classification 1B is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 1000 V.

11. Abbreviations

Table 12. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
GEN9	Ninth Generation
GSM	Global System for Mobile Communications
LDMOS	Laterally Diffused Metal Oxide Semiconductor
LTE	Long Term Evolution
MMIC	Monolithic Microwave Integrated Circuit
MTF	Median Time to Failure
ОВО	Output Back Off
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

12. Revision history

Table 13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLM9D2327-25B v.1	20170901	Product data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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BLM9D2327-25B

LDMOS 2-stage integrated Doherty MMIC

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